

FORM PTO-1449

LIST OF DOCUMENTS CITED BY APPLICANT

JUN 02 2004

Atty. Docket No.

A-8753W

Appln. No.

10/742,890

Applicant

Gerald J. BANKS

Filing Date

December 23, 2003

Group

2818

U.S. PATENT DOCUMENTS

Examiner Initial		Document Number	Date	Name	Class	Sub-class	Filing Date
HN	AA	5,200,920	04/06/93	Norman et al.	365	185	
HN	AB	Re 32,401	04/14/87	Belistein, Jr. et al	365	182	
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						

FOREIGN PATENT DOCUMENTS

Examiner Initial		Document Number	Date	Country	Class	Sub-class	Translation
HN	AL	56-114199	09/08/81	Japan			No
HN	AM	61-239497	10/24/86	Japan			No
HN	AN	61-239498	10/24/86	Japan			No
HN	AO	62-24499	02/02/87	Japan			No
HN	AP	1-159895	06/22/89	Japan			No
	AQ						

OTHER REFERENCES

HN	AR	Torelli, Guido et al., "An Improved Method for Programming a Word-Erasable EEPROM", <u>Alta Frequenza - Scientific Review in Electronics</u> , Vol. LII, No. 6, Pages 487-494 (1983).
HN	AS	Yoshikawa, Kuniyoshi et al., "An Asymmetrical Lightly-Doped Source (ALDS) Cell for Virtual Ground High Density EPROMs", <u>IEEE International Electron Devices Meeting</u> , 1988, Pages 432-435.

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Examiner Initial		Document Number	Date	Name	Class	Sub-class	Filing Date
HN	AA	4,417,325	11/22/83	Harari	365	185	
↑	AB	4,448,400	5/15/84	Harari	365	185	
	AC	4,612,629	9/16/86	Harari	365	185	
	AD	5,043,940	8/27/91	Harari	365	168	
	AE	5,163,021	11/10/92	Mehrotra et al.	365	185	
	AF	5,168,465	12/1/92	Harari	257	320	
	AG	5,198,380	3/30/93	Harari	437	43	
	AH	5,200,959	4/6/93	Gross et al.	371	21.6	
	AI	5,268,318	12/7/93	Harari	437	43	
	AJ	5,268,319	12/7/93	Harari	437	43	
	AK	5,268,870	12/7/93	Harari	365	218	
	AL	5,272,669	12/21/93	Samachisa et al.	365	185	
	AM	5,293,560	3/8/94	Harari	365	185	
	AN	5,313,421	5/17/94	Guterman et al.	365	185	
	AO	5,422,842	6/6/95	Cernea et al.	365	185	
	AP	5,428,621	6/27/95	Mehrotra et al.	371	21.4	
	AQ	5,430,859	7/4/95	Norman et al.	395	425	
	AR	5,434,825	7/18/95	Harari	365	185	
	AS	5,495,442	2/27/96	Cernea et al.	365	185.03	
	AT	5,544,118	8/6/96	Harari	365	218	
	AU	5,554,553	9/10/96	Harari	437	43	
	AV	5,568,439	10/22/96	Harari	365	218	
	AW	5,583,812	12/10/96	Harari	365	185.33	
	AX	5,642,312	6/24/97	Harari	365	185.33	
Y	AY	5,657,332	8/12/97	Auclair et al.	371	40.11	
HN	AZ	5,659,550	8/19/97	Mehrotra et al.	371	21.4	

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Examiner Initial		Document Number	Date	Name	Class	Sub-class	Filing Date
HN	BA	5,712,180	1/27/98	Guterman et al.	437	43	
↑	BB	5,712,819	1/27/98	Harari	365	185.29	
	BC	5,776,810	7/7/98	Guterman et al.	438	258	
	BD	5,806,070	9/8/98	Norman et al.	711	103	
	BE	4,661,929	4/285/87	Aoki et al.	365	189	
	BF	4,701,884	10/20/87	Aoki et al.	365	189	
	BG	4,709,350	11/24/87	Nakagome et al.	365	45	
	BH	5,014,242	5/7/91	Akimoto et al.	365	63	
	BI	5,299,165	3/29/94	Kimura et al.	365	210	
	BJ	5,307,304	4/26/94	Saito et al.	365	145	
	BK	5,802,553	9/1/98	Robinson et al.	711	103	
	BL	5,801,991	9/1/98	Keeney et al.	365	185.23	
	BM	5,796,667	8/18/98	Sweha et al.	365	207	
	BN	5,781,472	7/14/98	Sweha et al.	365	185.11	
	BO	5,754,566	5/19/98	Christopherson et al.	371	40.18	
	BP	5,748,546	5/5/98	Bauer et al.	365	210	
	BQ	5,671,388	9/23/97	Hasbun	395	430	
	BR	5,574,879	11/12/96	Wells et al.	395	427	
	BS	5,566,125	10/15/96	Fazio et al.	365	45	
	BT	5,563,828	10/8/96	Hasbun et al.	365	185.33	
	BU	5,553,020	9/3/96	Keeney et al.	365	185.19	
	BV	5,546,042	8/13/96	Tedrow et al.	327	538	
	BW	5,497,354	3/5/96	Sweha et al.	365	230.06	
✓	BX	5,487,033	1/23/96	Keeney et al.	365	185.19	
HN	BY	5,438,546	8/1/95	Ishac et al.	365	200	

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HN	AA	4,192,014	03/04/80	Craycraft	365	104	
↑	AB	4,357,685	11/02/82	Daniele et al.	365	189	
	AC	4,964,079	10/16/90	Devin	365	168	
	AD	5,172,338	12/15/92	Mehrotra et al.	365	185	
	AE	5,262,984	11/16/93	Noguchi et al.	365	185	
	AF	3,801,965	04/02/74	Keller et al.	340	173R	
	AG	4,004,159	01/18/77	Rai et al.	307	238	
	AH	4,054,864	10/18/77	Audaire et al.	340	173R	
	AI	4,090,258	05/16/78	Cricchi	365	184	
↓	AJ	4,122,541	10/24/78	Uchida	365	154	
HN	AK	4,139,910	02/13/79	Anantha et al.	365	183	

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Examiner Initial		Document Number	Date	Country	Class	Sub-class	Translation
HN	AL	WO82/02276	07/08/82	WIPO			
↑	AM	WO82/02976	09/02/82	WIPO			
	AN	WO90/01984	03/08/90	WIPO			
	AO	2 630 574	10/27/89	France			Abstract
↓	AP	0 390 404	10/03/90	Europe			
HN	AQ	0 725 403	08/07/96	EPO			

OTHER PUBLICATIONS

HN	AR	M. Bauer et al., A Multilevel-Cell 32Mb Flash Memory, 1995 IEEE International Solid-State Circuits Conference, Session 7, Paper TA7.7.
HN	AS	John A. Bayliss et al., The Interface Processor for the 32b Computer, 1981 IEEE International Solid-State Circuits Conference, February 1981, at 116-117.

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Examiner Initial		Document Number	Date	Name	Class	Sub-class	Filing Date
HN	AA*	4,149,270	04/10/79	Cricchi et al.	365	222	
↑	AB*	4,181,980	01/01/80	McCoy	365	45	
	AC*	4,272,830	06/09/81	Moench	365	45	
	AD*	4,287,570	09/01/81	Stark	365	104	
	AE*	4,300,210	11/10/81	Chakravarti et al.	365	45	
	AF*	4,306,300	12/15/81	Terman et al.	365	45	
	AG*	4,327,424	04/27/82	Wu	365	104	
	AH*	4,388,702	06/14/83	Sheppard	365	104	
	AI*	4,415,992	11/15/83	Adlhoch	365	94	
↓	AJ*	4,449,203	05/15/84	Adlhoch	365	104	
HN	AK*	4,462,088	07/24/84	Giuliani et al.	365	105	

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Examiner Initial		Document Number	Date	Country	Class	Sub-class	Translation
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	AN*						
	AO*						
	AP*						
	AQ*						

OTHER CITATIONS INCLUDING AUTHOR, TITLE, DATE, PUBLICATION, PAGES, ETC.

HN	AR*	Christoph Bleiker & Hans Melchior, A Four-State EEPROM Using Floating-Gate Memory Cells, IEEE Journal of Solid-State Circuits, Vol. SC-22, No. 3, June 1987, at 260-263.
HN	AS*	Raymond A. Heald & David A. Hodges, Multilevel Random-Access Memory Using One Transistor Per Cell, IEEE Journal of Solid-State Circuits, Vol. SC-11, No. 4, August 1976, at 519-528.

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HN	AA^	4,495,602	01/22/85	Sheppard	365	104	
	AB^	4,503,518	03/05/85	Iwahashi	365	104	
	AC^	4,558,241	12/10/85	Suzuki et al.	307	530	
	AD^	4,578,777	03/25/86	Fang et al.	365	184	
	AE^	4,586,163	04/29/86	Koike	365	104	
	AF^	4,627,027	12/02/86	Rai et al.	365	45	
	AG^	4,653,023	03/24/87	Suzuki et al.	365	104	
	AH^	4,661,929	04/28/87	Aoki et al.	365	189	
	AI^	4,709,350	11/24/87	Nakagome et al.	365	45	
	AJ^	4,733,394	03/22/88	Giebel	371	21	
HN	AK^	4,771,404	09/13/88	Mano et al.	365	189	

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	AM^						
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HN	AR^	David A. Rich, A Survey of Multivalued Memories, IEEE Transactions on Computers, Vol. C-35, No. 2, February 1986, at 99-106.
HN	AS^	R.S. Withers et al., Nonvolatile Analog Memory in MNOS Capacitors, IEEE Electron Device Letters, Vol. EDL-1, No. 3, March 1980, at 42-45.

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HN	AA#	4,799,195	01/17/89	Iwahashi et al.	365	185	
A	AB#	4,847,808	07/11/89	Kobatake	364	104	
	AC#	4,853,892	08/01/89	Hori	365	49	
	AD#	4,890,259	12/26/89	Simko	365	45	
	AE#	4,914,631	04/03/90	Johnson et al.	365	189.11	
	AF#	4,989,179	01/29/91	Simko	365	45	
	AG#	5,021,999	06/04/91	Kohda et al.	365	168	
	AH#	5,043,940	08/27/91	Harari	365	168	
	AI#	5,095,344	03/10/92	Harari	357	23.5	
V	AJ#	5,163,021	11/10/92	Mehrotra et al.	365	185	
HN	AK#	5,258,958	11/02/93	Iwahashi et al.	365	210	

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	AO#						
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HN	AR#	"Mid-Level Current Generator Circuit", IBM Technical Disclosure Bulletin, Vol. 33, No. 1B, 1 June 1990, pp. 386-388.
	AS#	
	AT#	

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HN	AA'	5,268,870	12/07/93	Harari	365	218	
↑	AB'	5,293,560	03/08/94	Harari	365	185	
	AC'	5,321,655	06/14/94	Iwahashi et al.	365	200	
	AD'	5,351,210	09/27/94	Saito	365	189.01	
	AE'	5,422,845	06/06/95	Ong	365	185	
	AF'	5,432,735	07/11/95	Parks et al.	365	168	
	AG'	5,434,825	07/18/95	Harari	365	185	
	AH'	5,440,505	08/08/95	Fazio et al.	365	45	
	AI'	5,444,656	08/22/95	Bauer et al.	365	189.01	
↓	AJ'	5,450,363	09/12/95	Christopherson et al.	365	205	
HN	AK'	5,457,650	10/10/95	Sugiura et al.	365	184	

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HN	AA-	5,469,384	11/21/95	Lacey	365	185.13	
↑	AB-	5,475,693	12/12/95	Christopherson et al.	371	10.2	
	AC-	5,485,422	01/16/96	Bauer et al.	365	168	
	AD-	5,497,119	03/05/96	Tedrow et al.	327	540	
	AE-	5,506,813	04/09/96	Mochizuki et al.	365	230.03	
	AF-	5,508,958	04/16/96	Fazio et al.	365	185.19	
	AG-	5,515,317	05/07/96	Wells et al.	395	427	
	AH-	5,523,972	06/04/96	Rashid et al.	365	185.22	
	AI-	5,539,690	07/23/96	Talreja et al.	365	185.22	
↓	AJ-	5,541,886	07/30/96	Hasbun	365	230.01	
HN	AK-	5,544,118	08/06/96	Harari	365	218	

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HN	AC❖	5,583,812	12/10/96	Harari	365	185.33	
HN	AD❖	5,594,691	01/14/97	Bashir	365	189.09	
HN	AE❖	5,596,527	01/21/97	Tomioka et al.	365	185.20	
HN	AF❖	3,660,819	05/02/72	Frohman-Bentchkowsky	317	235R	
HN	AG❖	5,295,255	03/15/94	Malecek et al.	395	425	
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HN	AB	5,021,999	6/4/91	Kohda et al.	365	168	
HN	AC	4,903,236	2/20/90	Nakayama et al.	365	185	
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HN	AQ	Bleiker, Christoph, and Melchior, Hans. "A Four-State EEPROM Using Floating-Gate Memory Cells." IEEE Journal of Solid-State Circuits, Vol. SC-22, No. 3. (June 1987) : 460-463.					
HN	AR	Intel Corporation. "2764A Advanced 64K (8K x 8) Production and UV Erasable PROMs." Memory Components Handbook. (October 1985) : 4.10-4.20.					
HN	AS	Chi, Min-hwa, and Bergemont, Albert. "Multi-level Flash/EPROM Memories: New Self-convergent Programming Methods for Low-voltage Applications." 1995 Technical Digest-International Electron Devices Meeting. (1995) : 271-274.					

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HN	BQ	Aritome, Seiichi, et al. "A Novel Side-Wall Transfer-Transistor Cell (SWATT Cell) For Multi-Level NAND EEPROMs." 1995 Technical Digest-International Electron Devices Meeting. (1995) : 275-278.
HN	BR	Bauer, M., et al. "TA 7.7: A Multilevel-Cell 32Mb Flash Memory." 1995 IEEE International Solid-State Circuits Conference, 1995 Digest of Technical Papers. (1995) : 132-133.
HN	BS	Hemink, G.J., et al. "Fast and Accurate Programming Method for Multi-level NAND EEPROMs." 1995 Symposium on VLSI Technology Digest of Technical Papers. (1995) : 129-130.

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HN	CR	Gotou, Hiroshi. "New Operation Mode for Stacked-Gate Flash Memory Cell." IEEE Electron Device Letters, Vol. 16, No. 3. (March 1995) : 121-123.
HN	CS	Jung, Tae-Sung, et al. "TP 2.1: A 3.3V 128Mb Multi-Level NAND Flash Memory for Mass Storage Applications." 1996 IEEE International Solid-State Circuits Conference, 1996 Digest of Technical Papers. (1996) : 32-33.

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HN	DQ	Neale, Ron. "Will multi-level Flash memory be the way to the future?" Electronic Engineering (London), Vol. 68, No. 835. (July 1996): 3 pp.
HN	DR	Patton, Robert. "Flash makers taking conservative steps forward." Japanese Press Network. (November 1996) : 2 pp.
HN	DS	Ohkawa, Masayoshi, et al. "TP 2.3: A 98mm ² 3.3V 64Mb Flash Memory with FN-NOR Type 4-level Cell." 1996 IEEE International Solid-State Circuits Conference, 1996 Digest of Technical Papers. (1996) : 36-37.

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FOREIGN PATENT DOCUMENTS

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HN	EQ	Montanari, D., et al. "Multi-Level Charge Storage in Source-Side Injection Flash EEPROM." 1996 IEEE International NonVolatile Memory Technology Conference. (1996) : 80-83.
HN	ER	Atwood, Greg, et al. "Intel StrataFlash Memory Technology Overview." Intel Technology Journal. (Fourth quarter 1997) : 1-8.
HN	ES	Fazio, Al, and Bauer, Mark. "Intel StrataFlash Memory Technology Development and Implementation." Intel Technology Journal. (Fourth quarter 1997) : 1-13.

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HN	FR	Candelier, Ph., et al. "Hot Carrier Self Convergent Programming Method for Multi-Level Flash Cell Memory." 1997 35 th Annual IEEE International Reliability Physics Symposium. (1997) : 104-109.					
HN	FS	Intel Corporation. "Intel StrataFlash Memory Technology 32 and 64 Mbit." Intel Advance Information. (January 1998) : 1-53.					

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HN	GR	Blyth, Trevor, et al. "TPM 11.7: A Non-Volatile Analog Storage Device Using EEPROM Technology." 1991 IEEE International Solid-State Circuits Conference, Digest of Technical Papers. (February 1991) : 192-193 and 315.
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	IA						
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HN	JR	Yoshikawa, Kuniyoshi. "Impact of Cell Threshold Voltage Distribution in the Array of Flash Memories on Scaled and Multilevel Flash Cell Design." 1996 Symposium on VLSI Technology Digest of Technical Papers. (1996) : 240-241.
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	KA						
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HN	LR	Aritome, Seiichi, et al. "A Side-Wall Transfer-Transistor Cell (SWATT Cell) for Highly Reliable Multi-Level NAND EEPROM's." IEEE Transactions on Electron Devices, Vol. 44, No. 1. (January 1997) : 145-152.
HN	LS	Gotou, H. "An Experimental Confirmation of Automatic Threshold Voltage Convergence in a Flash Memory Using Alternating Word-Line Voltage Pulses." IEEE Electron Device Letters, Vol. 18, No. 10. (October 1997) : 503-505.

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HN	NS	Hanyu, Takahiro, et al. "TP 2.5: 2-Transistor-Cell 4-Valued Universal-Literal CAM for a Cellular Logic Image Processor." 1997 IEEE International Solid-State Circuits Conference. (February 1997) : 46-47 and 362.

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HN	PR	Bonner, Bruce. "New Flash Market Attracts SGS and Mitsubishi." Dataquest, The Semiconductor DQ Monday Report, Issue 8. (March 2, 1998). Dataquest Analysis provided only.
HN	PS	Donoghue, Bill, et al. "A 256K HCMOS ROM Using a Four-State Cell Approach." IEEE Journal of Solid-State Circuits, Vol. SC-20, No. 2. (April 1985) : 598-602.

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<u>LIST OF DOCUMENTS CITED BY APPLICANT</u>				Applicant Gerald J. BANKS			
				Filing Date December 23, 2003		Group 2818	
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	AS	6,434,050	08/13/02	Banks	365	185.2	
	AT	6,381,172	04/30/02	Banks	365	185.03	
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OTHER (including author, title, date, pertinent pages, etc.)							
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Examiner HIEN NGUYEN				Date Considered 3/4/05			
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				Applicant Gerald J. BANKS			
				Filing Date December 23, 2003		Group 2824	
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HN	AJ	9-181279	07/11/97	Japan			No
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HN	AL	5-217385,	08/27/93	Japan			No
HN	AM	3-242898,	10/29/91	Japan			No
HN	AN	6-68682/	03/11/94	Japan			Abstract
HN	AO	8-195092/	07/30/96	Japan			Abstract
HN	AP	62-6493,	01/13/87	Japan			Abstract
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A-8753W
PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

Gerald J. BANKS

Appln. No.: 10/742,890

Group Art Unit: 2824

Filed: December 23, 2003

Examiner: H. Nguyen

For: MEMORY APPARATUS INCLUDING PROGRAMMABLE NON-VOLATILE
MULTI-BIT MEMORY CELL, AND APPARATUS AND METHOD FOR
DEMARCATING MEMORY STATES OF CELL

Allowed: May 18, 2004

Confirmation No.: 7102

* * *

SECOND

REQUEST FOR ACKNOWLEDGEMENT OF INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Attn: Mail Stop Issue Fee

Sir:

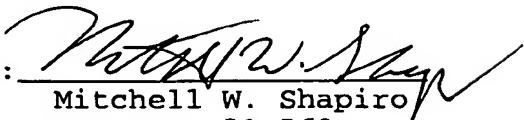
An Information Disclosure Statement was filed on May
17, 2004, prior to the allowance of the subject application.

Applicant respectfully requests that the Examiner
confirm consideration of the Information Disclosure



Statement by returning an endorsed copy of the Form PTO-
1449.

Respectfully submitted,

By: 
Mitchell W. Shapiro
Reg. No. 31,568

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August 18, 2004